

ABSTRACT OF THE DISCLOSURE

A non-volatile semiconductor memory device includes an electrically data rewritable non-volatile semiconductor memory cell and a write circuit for
5 writing data in the memory cell, the write circuit writing a data in the memory cells by supplying a write voltage V_{pgm} and a write control voltage VBL to the memory cell, continuing the writing of the data in the memory cell by changing the value of the write control
10 voltage VBL in response to an advent of a first write state of the memory cell and inhibiting any operation of writing a data to the memory cell by further changing the value of the write control voltage VBL to
15 V_{dd} in response to an advent of a second write state of the memory cell.